

Figure 2. The growth rate (GR) of SiN films versus dosing times of silicon precursors (A – Si₂Cl₆, B – SiBr₄) in amine catalyzed PEALD-SiN (blue dots) and normal PEALD-SiN (orange dots) processes.

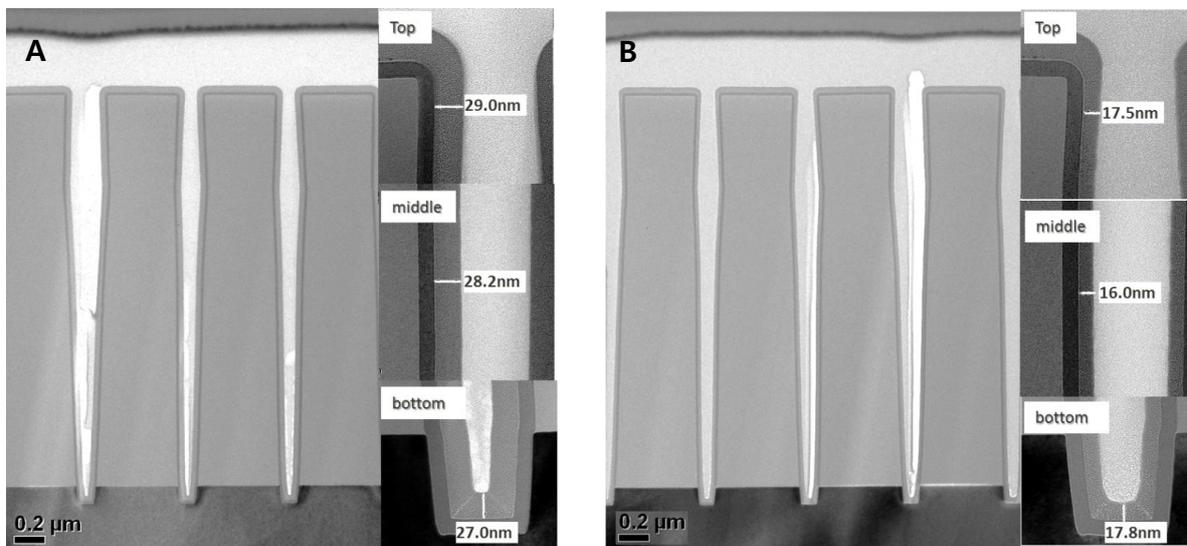


Figure 3. TEM images of a silicon nitride layer on the trench structure with high aspect ratio: (A) as-deposition and (B) post diluted HF etch process. (Silicon nitride film was deposited using Si₂Cl₆.)